NEC

MOS INTEGRATED CIRCUIT
μPD17P103

4 BIT SINGLE-CHIP MICROCONTROLLER

The μPD17P103 is a one-time PROM version of the μPD17103, in which the internal masked ROM of the μPD17103 is replaced with a one-time PROM that can be written to just once.

Since user programs can be written to the PROM, this microcontroller is suited for program evaluation and small-lot production of the μPD17103, or for program evaluation of the μPD17103(A), μPD17103(A1), μPD17103L, or μPD17103L(A).

When reading this document, refer to the publications on the μPD17103.

FEATURES

- 17K architecture : General registers
- Pin compatible with the μPD17103 (except for PROM programming function)
- Internal one-time PROM : 1K byte (512 × 16 bits)
- Instruction execution time : 2 μs (at f_X = 8 MHz, ceramic oscillation)
- Supply voltage : V_{DD} = 2.7 to 6.0 V (f_X = 500 kHz to 2 MHz)
  V_{DD} = 4.5 to 6.0 V (f_X = 500 kHz to 8 MHz)

APPLICATIONS

- Controlling electric appliances or toys
- Implementing circuitry consisting of general-purpose logic ICs, using a single chip

ORDERING INFORMATION

Part number	Package
μPD17P103CX	16-pin plastic DIP (300 mil)
μPD17P103GS	16-pin plastic SOP (300 mil)

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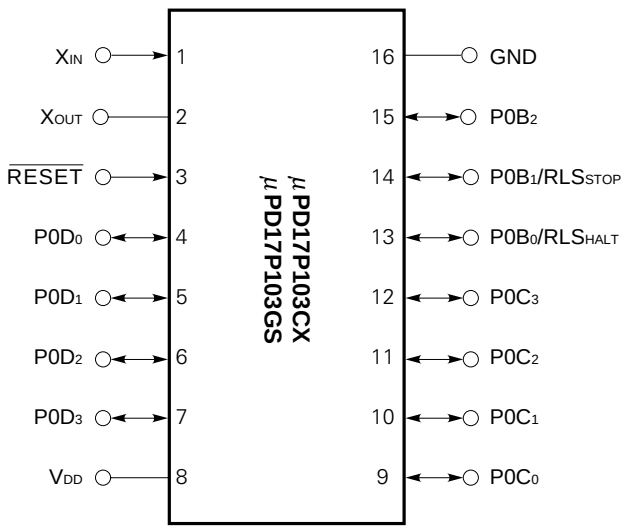
Date Published March 1996 P
Printed in Japan

The mark ★ shows major revised points.

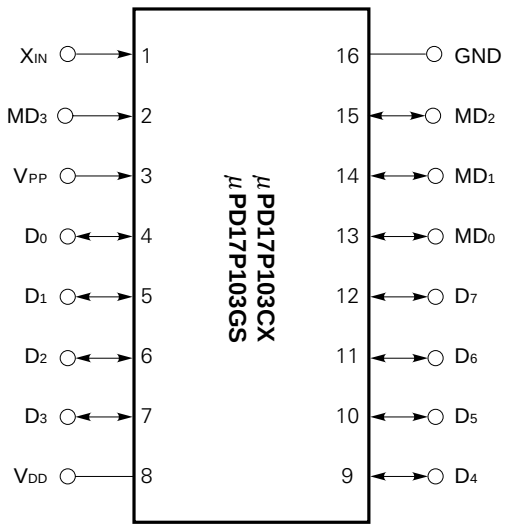
PIN CONFIGURATION (TOP VIEW)

16-pin plastic DIP
16-pin plastic SOP

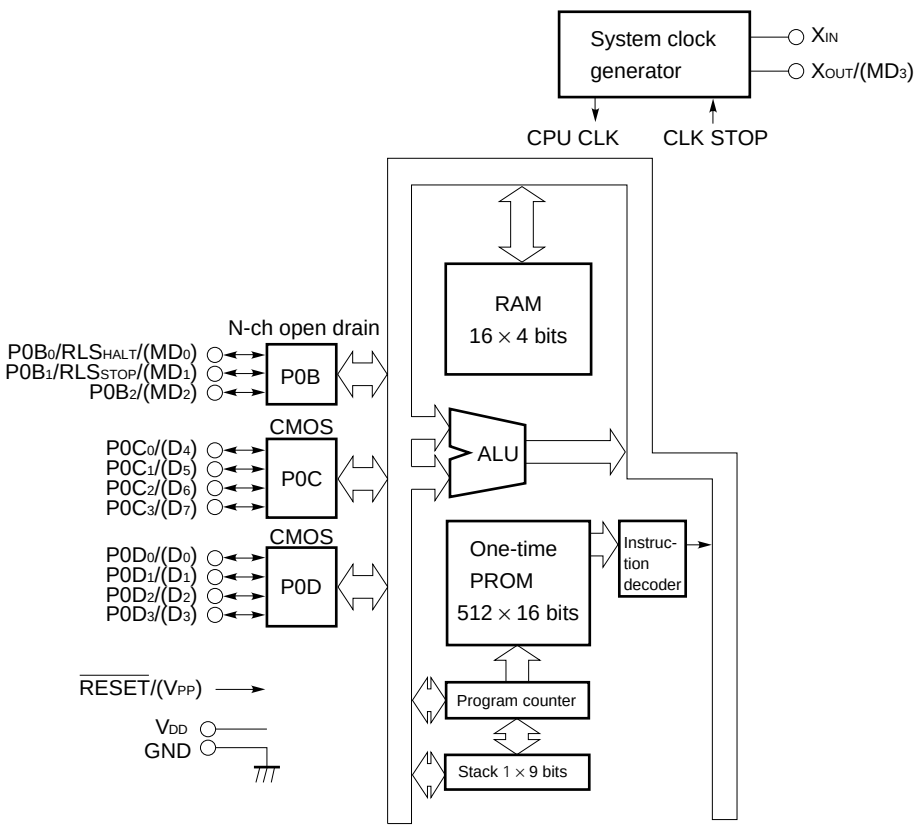
(1) Normal operation mode



(2) PROM programming mode



BLOCK DIAGRAM



Remark ( ): PROM programming mode

CONTENTS

1. PINS

1.1 PIN FUNCTIONS

- Port pins

Pin[Note]	I/O	Function	PROM programming mode	Upon reset
$P0B_0/RLS_{HALT}/(MD_0)$	I/O	For releasing HALT mode	Mode selection pin (MD_0-MD_2)	High impedance (input mode)
$P0B_1/RLS_{STOP}/(MD_1)$		For releasing STOP mode		
$P0B_2/(MD_2)$		• N-ch open-drain 3-bit I/O port (port 0B) • Withstand voltage of 9 V		
$P0C_0/(D_4)$ - $P0C_3/(D_7)$	I/O	• CMOS (push-pull) 4-bit I/O port (port 0C)	8-bit data I/O pin (D_4-D_7)	High impedance (input mode)
$P0D_0/(D_0)$ - $P0D_3/(D_3)$	I/O	• CMOS (push-pull) 4-bit I/O port (port 0D)	8-bit data I/O pin (D_0-D_3)	High impedance (input mode)

- Non-port pins

Pin[Note]	I/O	Function	PROM programming mode
$\overline{RESET}/(V_{PP})$	Input	System reset input pin	+12.5 V is applied to this pin (V_{PP}).
V_{DD}	—	Power supply pin	Power supply pin (V_{DD}). +6 V is applied to this pin.
GND	—	GND pin	GND pin
X_{IN}	—	Pins for system clock generation	Program memory address update
$X_{OUT}/(MD_3)$			Mode selection pin (MD_3)

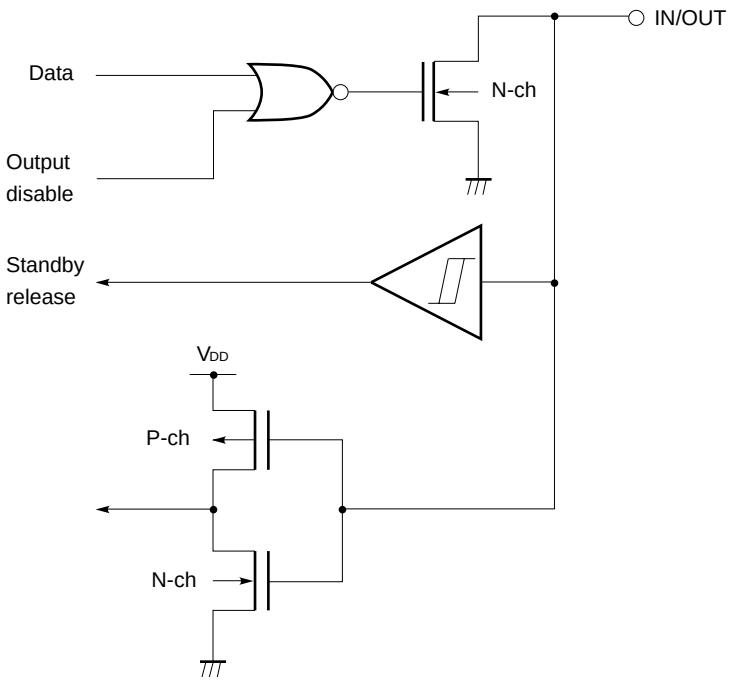
I/O: Input/output

Note Pin names in PROM programming mode are indicated in parentheses.

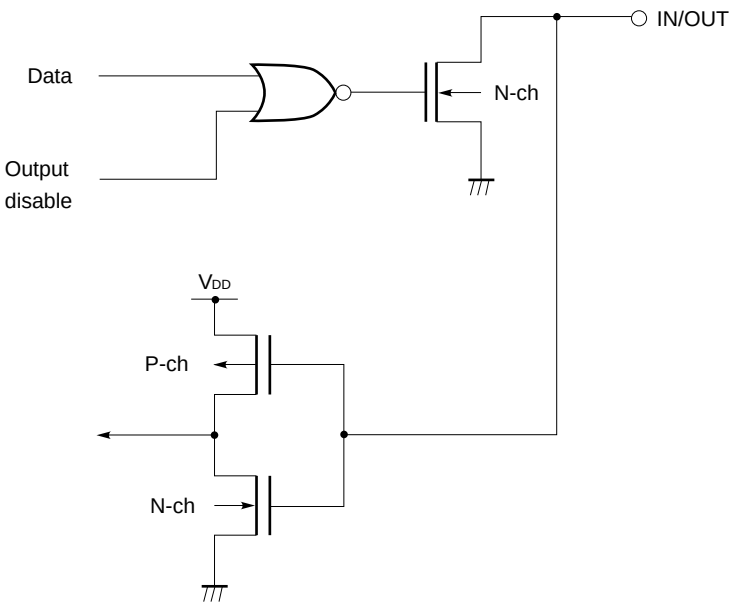
1.2 EQUIVALENT INPUT/OUTPUT CIRCUITS

Below are simplified diagrams of the equivalent input/output circuits.

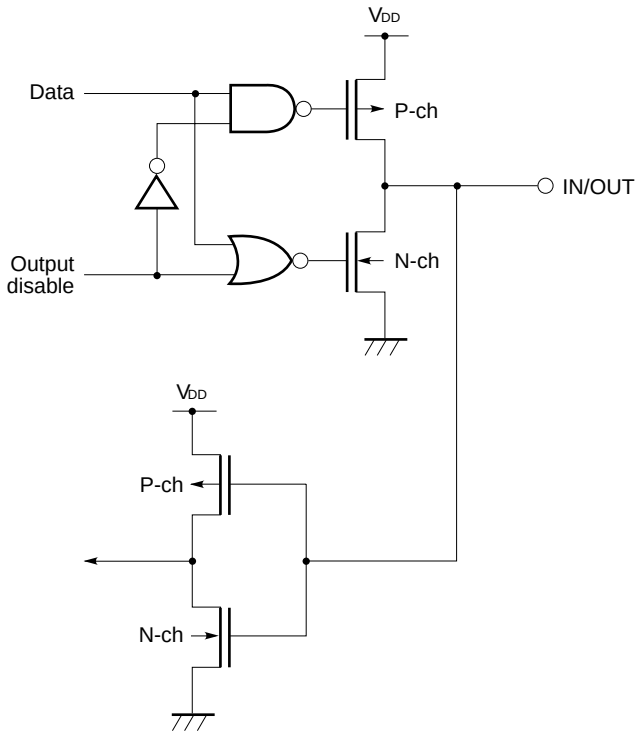
(1) $P0B_0$ and $P0B_1$



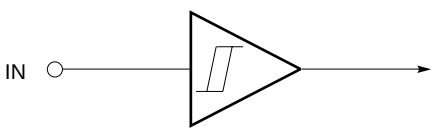
(2) $P0B_2$



(3) P0C and P0D



(4) $\overline{\text{RESET}}$



1.3 HANDLING UNUSED PINS

In normal operation mode, connect unused pins as follows:

Table 1-1 Handling Unused Pins

Pin			Recommended conditions and handling	
			Internal	External
Port	Input mode	P0B, P0C, P0D	—	Connect to V_{DD} or ground through resistors for each pin.**Note**
	Output mode	P0C, P0D (CMOS ports)	—	Leave open.
		P0B (N-ch open-drain port)	Outputs low level.	Leave open.

Note When a pin is pulled up to V_{DD} (connected to V_{DD} through a resistor) or pulled down to ground (connected to ground through a resistor) outside the chip, take the driving capacity and maximum current consumption of a port into consideration. When using high-resistance pull-up or pull-down resistors, apply appropriate countermeasures to ensure that noise is not attracted by the resistors. Although the optimum pull-up or pull-down resistor varies with the application circuit, in general, a resistor of 10 to 100 kilohms is suitable.

Caution To fix the output level of a pin, it is recommended that it should be specified repeatedly within a loop in a program.

1.4 NOTES ON USE OF THE $\overline{\text{RESET}}$ PIN (FOR NORMAL OPERATION MODE ONLY)

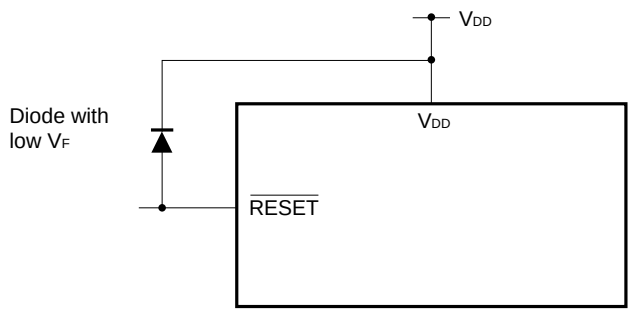
The $\overline{\text{RESET}}$ pin has the test mode selecting function for testing the internal operation of the μPD17P103 (IC test), besides the functions shown in **Section 1.1**.

Applying a voltage exceeding V_{DD} to the $\overline{\text{RESET}}$ pin causes the μPD17P103 to enter the test mode. When noise exceeding V_{DD} comes in during normal operation, the device is switched to the test mode.

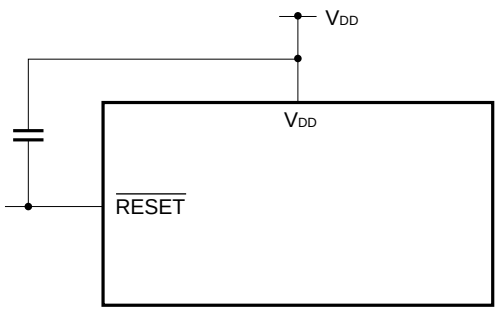
For example, if the wiring from the $\overline{\text{RESET}}$ pin is too long, noise may be induced on the wiring, causing this mode switching.

When installing the wiring, lay the wiring in such a way that noise is suppressed as much as possible. If noise yet arises, use an external part to suppress it as shown below.

- **Connect a diode with low V_F between the pin and V_{DD}.**



- **Connect a capacitor between the pin and V_{DD}.**



2. DIFFERENCES BETWEEN THE μPD17P103, μPD17103, AND μPD17103L

The μPD17P103 is a one-time PROM version of the μPD17103, in which the internal masked ROM is replaced with a one-time PROM.

Table 2-1 lists the differences between the μPD17P103, μPD17103, and μPD17103L.

The μPD17P103 has the same CPU functions and internal peripheral hardwares as those of μPD17103 and μPD17103L except for its program memory, mask option, oscillation settling time, and supply voltage range.

Part of electrical characteristics is also different between these products. For details of the electrical characteristics, refer to the data sheet of each product.

Table 2-1 Differences between the μPD17P103, μPD17103, and μPD17103L

Item	μPD17P103	μPD17103	μPD17103L
ROM	One-time PROM	Masked ROM	
	512 × 16 bits (0000H - 01FFH)		
Internal pull-up resistors of $P0B_0$ to $P0B_2$ pins	Not provided	Mask option	
Internal pull-up resistors of the $\overline{RESET}$ pin			
V_{PP} and operation mode selection pins	Provided	Not provided	
Oscillation settling time	$16/f_X$	$8/f_X$	
Supply voltage	V_{DD} = 2.7 to 6.0 V (at f_X = 500 kHz to 2 MHz) V_{DD} = 4.5 to 6.0 V (at f_X = 500 kHz to 8 MHz)		V_{DD} = 1.8 to 3.6 V (at f_X = 500 kHz to 2 MHz)
Quality grade	Standard	• Standard (μPD17103) • Special (μPD17103(A), μPD17103(A1))	• Standard (μPD17103L) • Special (μPD17103L(A))
★ Electrical characteristics	Partially differs between these products. Refer to the data sheet of each product for details.		

Cautions 1. Although a PROM product is highly compatible with a masked ROM product in respect of functions, they differ in internal ROM circuits and part of electrical characteristics. Before changing the PROM product to the masked ROM product in an application system, evaluate the system carefully using the masked ROM product.

★ **2. When the supply voltage and the resistance of a resistor mounted externally are the same, the oscillation frequency of the μPD17P103 is about 10 % lower than that of the μPD17103 or μPD17103L. Therefore, when the μPD17103 or μPD17103L is used instead of the μPD17P103, change the resistor externally mounted appropriately.**

3. WRITING TO AND VERIFYING ONE-TIME PROM (PROGRAM MEMORY)

The μPD17P103's internal program memory consists of a 512 × 16 bit one-time PROM.

Writing to the one-time PROM or verifying the contents of the PROM is accomplished using the pins shown in Table 3-1. Note that address inputs are not used; instead, the address is updated using the clock input from the X_{IN} pin.

Table 3-1 Pins Used When Writing to Program Memory or Verifying Its Contents

Pin name	Function
V_{PP}	Voltage (+12.5 V) is applied to this pin when writing to program memory or verifying its contents.
V_{DD}	Power supply pin. +6 V is applied to this pin when writing to program memory or verifying its contents.
$\overline{RESET}$	System reset input pin. Apply the specific signal to this pin to initialize the conditions of the microcontroller before switching to the program memory write/verify mode.
X_{IN}	Input pin for address update clocks used when writing to program memory or verifying its contents. Input of four pulses to this pin updates the address of the program memory.
MD_0 - MD_3	Input pins that select an operation mode when writing to program memory or verifying its contents
D_0 - D_7	Input/output pins for 8-bit data used when writing to program memory or verifying its contents

3.1 PROGRAM MEMORY WRITE/VERIFY MODES

If +6 V is applied to the V_{DD} pin and +12.5 V is applied to the V_{PP} pin after a certain duration of reset status (V_{DD} = 5 V, $\overline{RESET}$ = 0 V), the μPD17P103 enters program memory write/verify mode. A specific operating mode is then selected by setting the MD_0 through MD_3 pins as follows. Connect each pin not listed in Table 3-1 to ground through a pull-down resistor.

Table 3-2 Specification of Operating Modes

Operating mode specification						Operating mode
V_{PP}	V_{DD}	MD_0	MD_1	MD_2	MD_3	
+12.5 V	+6 V	H	L	H	L	Program memory address clear mode
		L	H	H	H	Write mode
		L	L	H	H	Verify mode
		H	×	H	H	Program inhibit mode

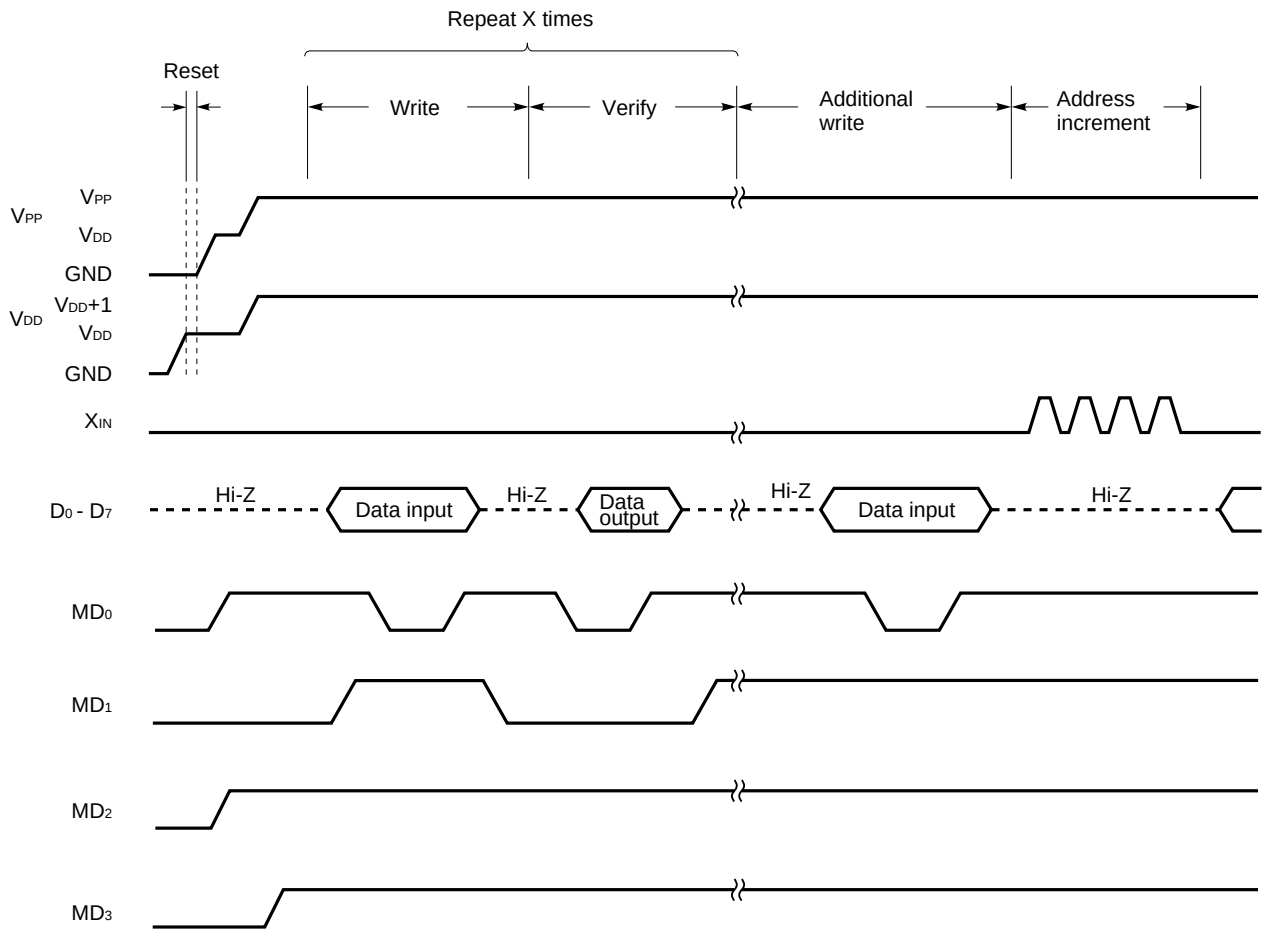
Remark ×: Don't care. L (low) or H (high)

3.2 WRITING TO PROGRAM MEMORY

The procedure for writing to program memory is described below; high-speed write is possible.

(1) Pull down the levels of all unused pins to GND by means of resistors. Bring the X_{IN} pin to low level.
(2) Apply 5 V to the V_{DD} pin and bring the V_{PP} pin to low level.
(3) Wait 10 μs. Then apply 5 V to the V_{PP} pin.
(4) Set the mode selection pins to program memory address clear mode.
(5) Apply 6 V to the V_{DD} pin and 12.5 V to the V_{PP} pin.
(6) Select program inhibit mode.
(7) Write data in 1-ms write mode.
(8) Select program inhibit mode.
(9) Select verify mode. If the write operation is found successful, proceed to step (10). If the operation is found unsuccessful, repeat steps (7) to (9).
(10) Perform additional write for X (number of repetitions of steps (7) to (9)) × 1 ms.
(11) Select program inhibit mode.
(12) Increment the program memory address by one on reception of four pulses on the X_{IN} pin.
(13) Repeat steps (7) to (12) until the last address is reached.
(14) Select program memory address clear mode.
(15) Apply 5 V to the V_{DD} and V_{PP} pins.
(16) Turn power off.

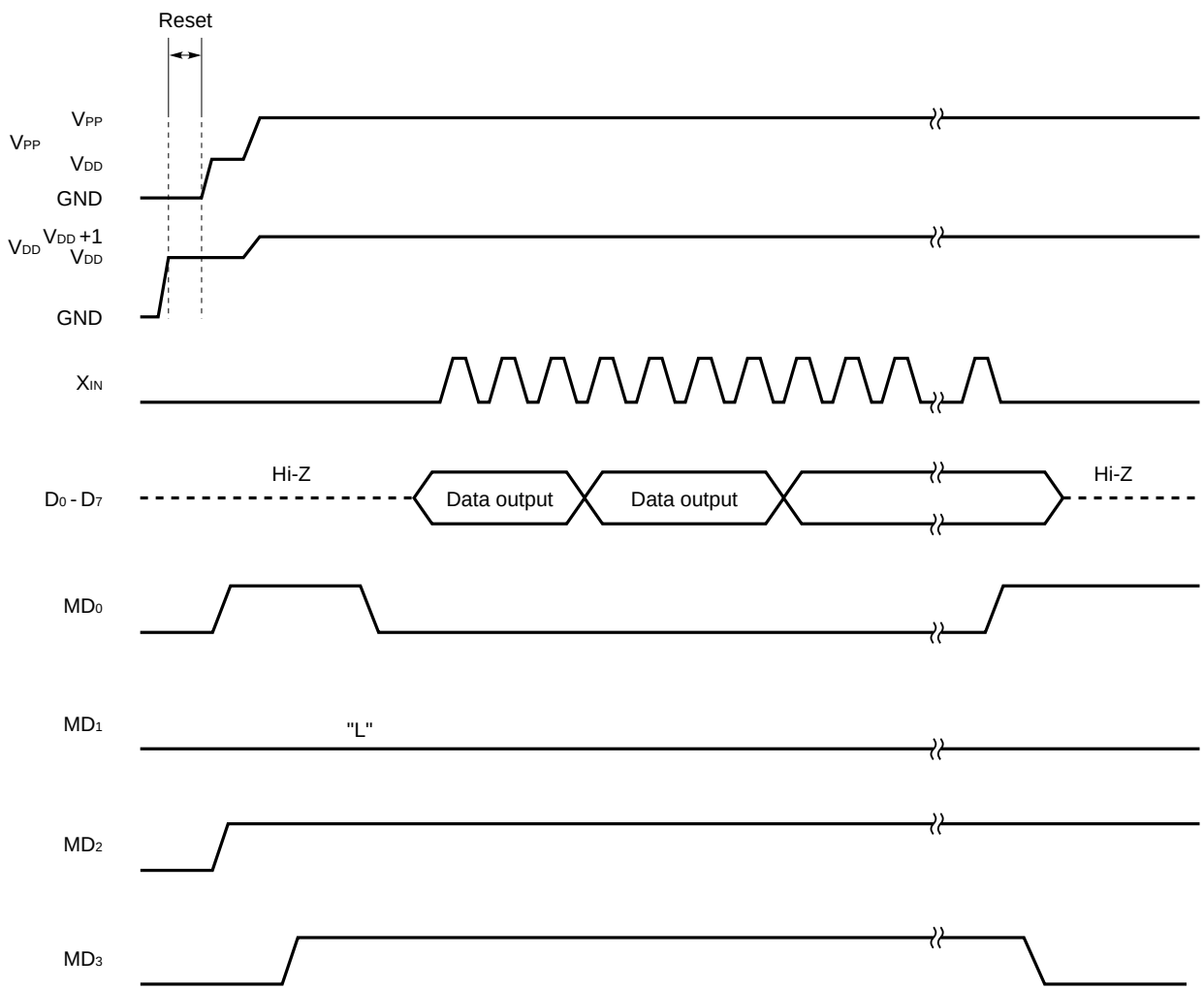
A timing chart for program memory writing steps (2) to (12) is shown below.



3.3 READING PROGRAM MEMORY

(1) Pull down the levels of all unused pins to GND by means of resistors. Bring the X_{IN} pin to low level.
(2) Apply 5 V to the V_{DD} pin and bring the V_{PP} pin to low level.
(3) Wait 10 μs. Then apply 5 V to the V_{PP} pin.
(4) Set the mode selection pins to program memory address clear mode.
(5) Apply 6 V to the V_{DD} pin and 12.5 V to the V_{PP} pin.
(6) Select program inhibit mode.
(7) Select verify mode. Data is output sequentially one address at a time for every four input clock pulses on the X_{IN} pin.
(8) Select program inhibit mode.
(9) Select program memory address clear mode.
(10) Apply 5 V to the V_{DD} and V_{PP} pins.
(11) Turn power off.

A timing chart for program memory reading steps (2) to (9) is shown below.



4. ELECTRICAL CHARACTERISTICS

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C)

Parameter	Symbol	Conditions		Rated value	Unit
Supply voltage	V_{DD}			−0.3 to +7.0	V
PROM supply voltage	V_{PP}			−0.3 to +13.5	V
Input voltage	V_I	P0C, P0D, $\overline{\text{RESET}}$		−0.3 to V_{DD} + 0.3	V
		P0B		−0.3 to +11	V
Output voltage	V_O	P0C, P0D		−0.3 to V_{DD} + 0.3	V
		P0B		−0.3 to +11	V
High-level output current	I_{OH}	Each of P0C and P0D		−5	mA
		Total of all output pins		−15	mA
Low-level output current	I_{OL}	Each of P0B, P0C, and P0D		30	mA
		Total of all output pins		100	mA
Operating ambient temperature	T_A			−40 to +85	°C
Storage temperature	T_{stg}			−65 to +150	°C
Allowable dissipation	P_d	T_A = 85°C	16-pin plastic DIP	400	mW
			16-pin plastic SOP	190	

Caution Absolute maximum ratings are rated values beyond which some physical damages may be caused to the product; if any of the parameters in the table above exceeds its rated value even for a moment, the quality of the product may deteriorate. Be sure to use the product within the rated values.

CAPACITANCE (T_A = 25 °C, V_{DD} = 0 V)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Input capacitance	C_{IN}	f = 1 MHz 0 V for pins other than pins to be measured			15	pF
I/O capacitance	C_{IO}				15	pF

I/O: Input/output

DC CHARACTERISTICS (T_A = –40 to +85 °C, V_{DD} = 2.7 to 6.0 V)

Parameter	Symbol	Conditions		Min.	Typ.	Max.	Unit
High-level input voltage	V_{IH1}	P0C, P0D		0.7V_{DD}		V_{DD}	V
	V_{IH2}	$\overline{\text{RESET}}$		0.8V_{DD}		V_{DD}	V
	V_{IH3}	P0B		0.8V_{DD}		9	V
Low-level input voltage	V_{IL1}	P0C, P0D		0		0.3V_{DD}	V
	V_{IL2}	P0B, $\overline{\text{RESET}}$		0		0.2V_{DD}	V
High-level output voltage	V_{OH1}	P0C, P0D V_{DD} = 4.5 to 6.0 V, I_{OH} = –2 mA		V_{DD} – 2.0			V
	V_{OH2}	P0C, P0D, I_{OH} = –200 μA		V_{DD} – 1.0			V
Low-level output voltage	V_{OL1}	P0B, P0C, P0D V_{DD} = 4.5 to 6.0 V, I_{OL} = 15 mA				2.0	V
	V_{OL2}	P0B, P0C, P0D, I_{OL} = 600 μA				0.5	V
High-level input leakage current	I_{LIH1}	P0B, P0C, P0D, V_{IN} = V_{DD}				5	μA
	I_{LIH2}	P0B, V_{IN} = 9 V				10	μA
Low-level input leakage current	I_{LIL}	P0B, P0C, P0D, V_{IN} = 0 V				–5	μA
High-level output leakage current	I_{LOH1}	P0B, P0C, P0D, V_{OUT} = V_{DD}				5	μA
	I_{LOH2}	P0B, V_{OUT} = 9 V				10	μA
Low-level output leakage current	I_{LOL}	P0B, P0C, P0D, V_{OUT} = 0 V				–5	μA
Power supply current	I_{DD1}	Operation mode	V_{DD} = 5 V ±10 %, f_X = 8.0 MHz		3.5	10.5	mA
			V_{DD} = 3 V ±10 %, f_X = 2.0 MHz		1.1	4.4	mA
	I_{DD2}	HALT mode	V_{DD} = 5 V ±10 %, f_X = 8.0 MHz		2.5	7.5	mA
			V_{DD} = 3 V ±10 %, f_X = 2.0 MHz		1.0	4.0	mA
	I_{DD3}	STOP mode	V_{DD} = 5 V ±10 %		10	50	μA
			V_{DD} = 3 V ±10 %		8	45	μA

CHARACTERISTICS OF DATA MEMORY FOR HOLDING DATA ON LOW SUPPLY VOLTAGE IN THE STOP MODE (T_A = –40 to +85 °C)

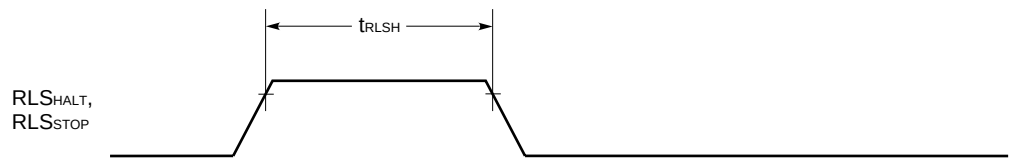
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Data hold supply voltage	V_{DDDR}		2.0		6.0	V
Data hold supply current	I_{DDDR}	V_{DDDR} = 2.0 V		0.1	5.0	μA

AC CHARACTERISTICS (T_A = –40 to +85 °C, V_{DD} = 2.7 to 6.0 V)

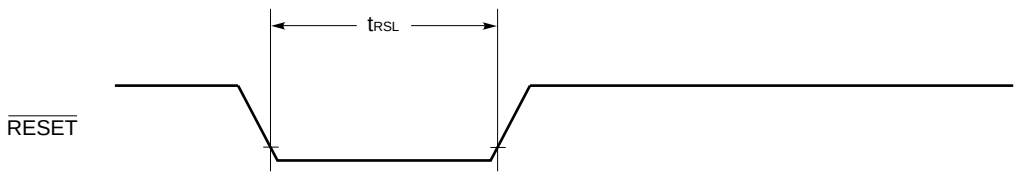
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
CPU clock cycle time (instruction execution time)	t_{CY}	V_{DD} = 4.5 to 6.0 V	1.9		33	μs
			7.6		33	μs
RLS_{HALT}, RLS_{STOP} high level width	t_{RLSH}		10			μs
$\overline{RESET}$ low level width	t_{RSL}		10			μs

Remark $t_{CY} = 16/f_X$ (f_X: frequency of system clock oscillator)

★ **RLS_{HALT} and RLS_{STOP} input timing**



$\overline{RESET}$ input timing



SYSTEM CLOCK OSCILLATOR CHARACTERISTICS (T_A = –40 to +85 °C, V_{DD} = 2.7 to 6.0 V)

Resonator	Parameter	Conditions	Min.	Typ.	Max.	Unit
Ceramic resonator	Oscillation frequency	V_{DD} = 2.7 to 6.0 V	0.49		2.04	MHz
		V_{DD} = 4.0 to 6.0 V	0.49		5.00	MHz
		V_{DD} = 4.5 to 6.0 V	0.49		8.16	MHz

DC PROGRAMMING CHARACTERISTICS (T_A = 25 °C, V_{DD} = 6.0 ±0.25 V, V_{PP} = 12.5 ±0.5 V)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Input voltage high	V_{IH1}	Except X_{IN}	0.7V_{DD}		V_{DD}	V
	V_{IH2}	X_{IN}	V_{DD} – 0.5		V_{DD}	V
Input voltage low	V_{IL1}	Except X_{IN}	0		0.3V_{DD}	V
	V_{IL2}	X_{IN}	0		0.4	V
Input leakage current	I_{LI}	V_{IN} = V_{IL} or V_{IH}			10	μA
Output voltage high	V_{OH}	I_{OH} = –1 mA	V_{DD} – 1.0			V
Output voltage low	V_{OL}	I_{OL} = 1.6 mA			0.4	V
V_{DD} power supply current	I_{DD}				30	mA
V_{PP} power supply current	I_{PP}	MD0 = V_{IL}, MD1 = V_{IH}			30	mA

Cautions 1. V_{PP} must be under +13.5 V including overshoot.

2. V_{DD} must be applied before V_{PP} on and must be off after V_{PP} off.

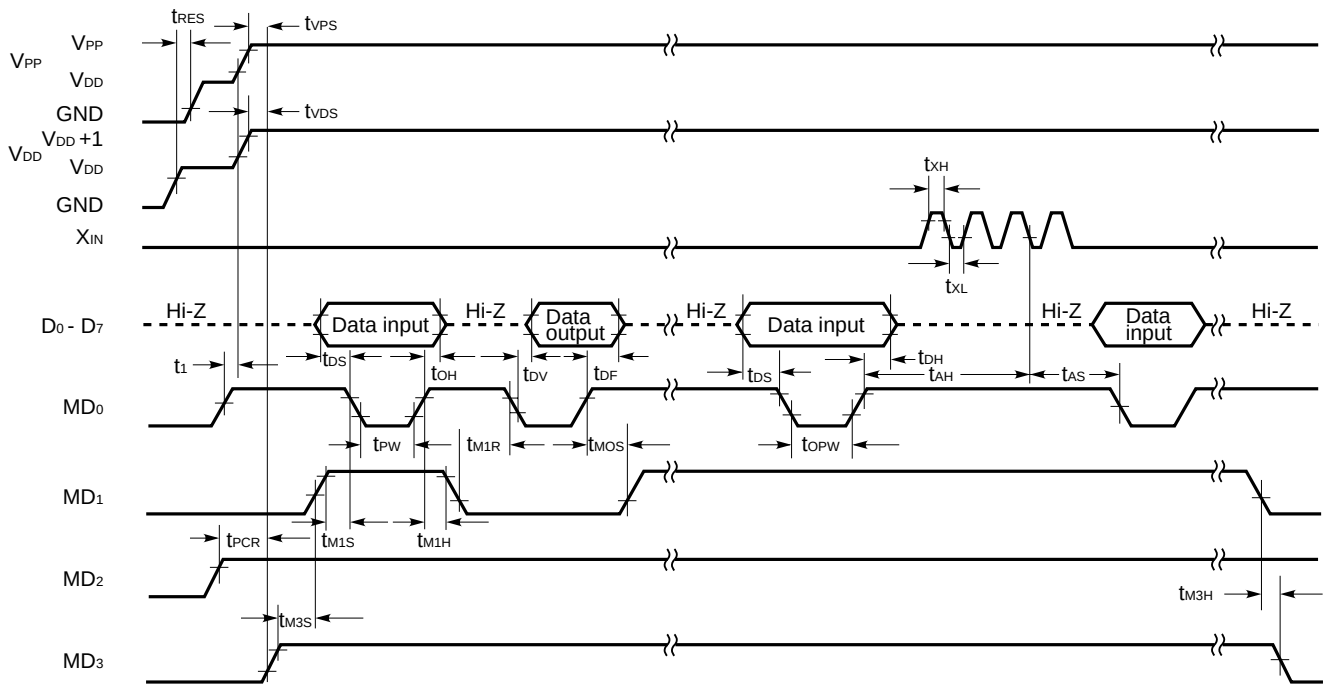
AC PROGRAMMING CHARACTERISTICS (T_A = 25 °C, V_{DD} = 6.0 ±0.25 V, V_{PP} = 12.5 ±0.5 V)

Parameter	Symbol	**Note 1**	Conditions	Min.	Typ.	Max.	Unit
Address setup time **Note 2** to MD_0↓	t_{AS}	t_{AS}		2			μs
MD_1 setup time to MD_0↓	t_{M1S}	t_{OES}		2			μs
Data setup time to MD_0↓	t_{DS}	t_{DS}		2			μs
Address hold time **Note 2** to MD_0↑	t_{AH}	t_{AH}		2			μs
Data hold time to MD_0↑	t_{DH}	t_{DH}		2			μs
Delay from MD_0↑ to data output float	t_{DF}	t_{DF}		0		130	ns
V_{PP} setup time to MD_3↑	t_{VPS}	t_{VPS}		2			μs
V_{DD} setup time to MD_3↑	t_{VDS}	t_{VCS}		2			μs
Initial program pulse width	t_{PW}	t_{PW}		0.95	1.0	1.05	ms
Additional program pulse width	t_{OPW}	t_{OPW}		0.95		21.0	ms
MD_0 setup time to MD_1↑	t_{MOS}	t_{CES}		2			μs
Delay from MD_0↓ to data output	t_{DV}	t_{DV}	MD0 = MD1 = V_{IL}			1	μs
MD_1 hold time to MD_0↑	t_{M1H}	t_{OEH}	$t_{M1H} + t_{M1R}$ • 50 μs	2			μs
MD_1 recovery time to MD_0↓	t_{M1R}	t_{OR}		2			μs
Program counter reset time	t_{PCR}	–		10			μs
X_{IN} input high, low level range	t_{XH}, t_{XL}	–		0.125			μs
X_{IN} input frequency	f_X	–				8	MHz
Initial mode set time	t_I	–		2			μs
MD_3 setup time to MD_1↑	t_{M3S}	–		2			μs
MD_3 hold time to MD_1↓	t_{M3H}	–		2			μs
MD_3 setup time to MD_0↓	t_{M3SR}	–	Read program memory	2			μs
Delay from address **Note 2** to data output	t_{DAD}	t_{ACC}	Read program memory			2	μs
Hold time from address **Note 2** to data output	t_{HAD}	t_{OH}	Read program memory	0		130	ns
MD_3 hold time to MD_0↑	t_{M3HR}	–	Read program memory	2			μs
Delay from MD_3↓ to data output float	t_{DFR}	–	Read program memory			2	μs
Reset setup time	t_{RES}			10			μs

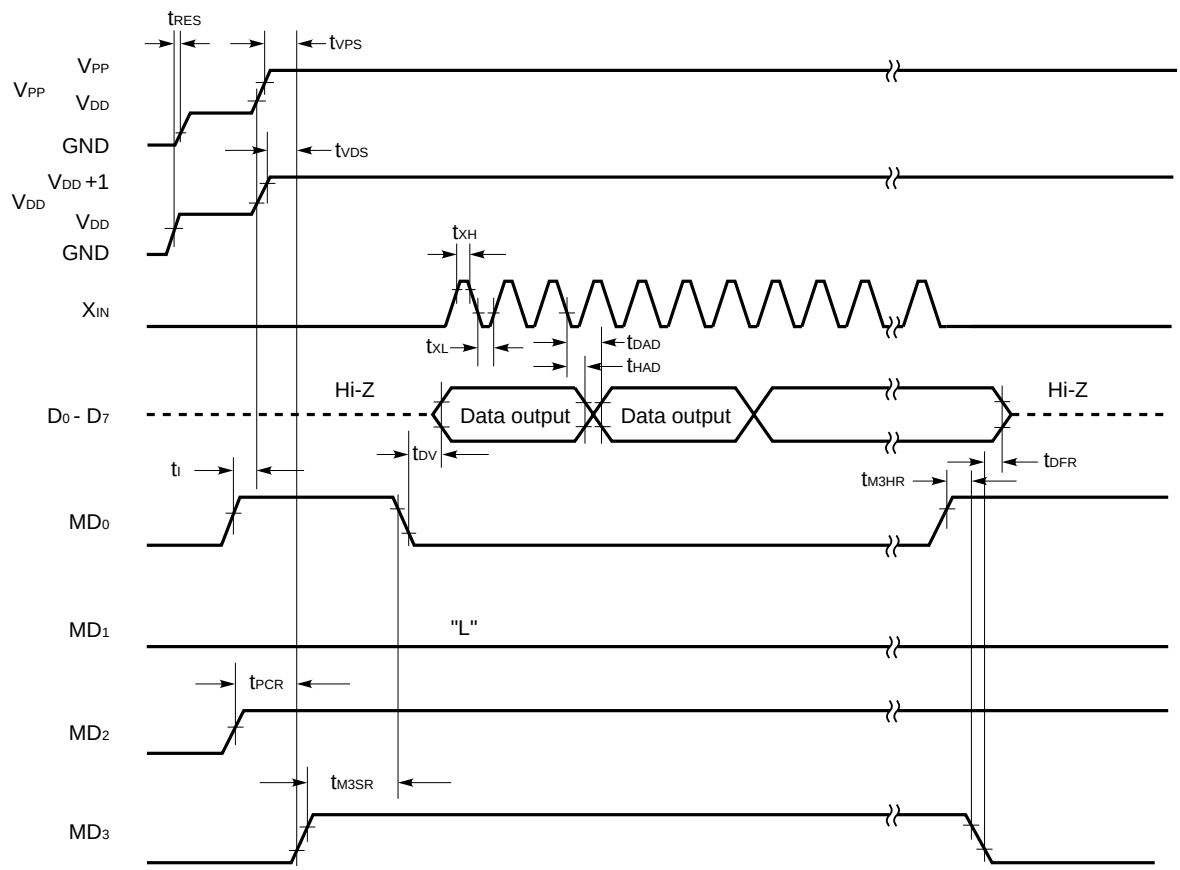
Notes 1. Symbols used for μPD27C256A (The μPD27C256A is used for maintenance.)

2. The internal address is incremented by one at the falling edge of the third clock (X_{IN}) input.

Write program memory timing

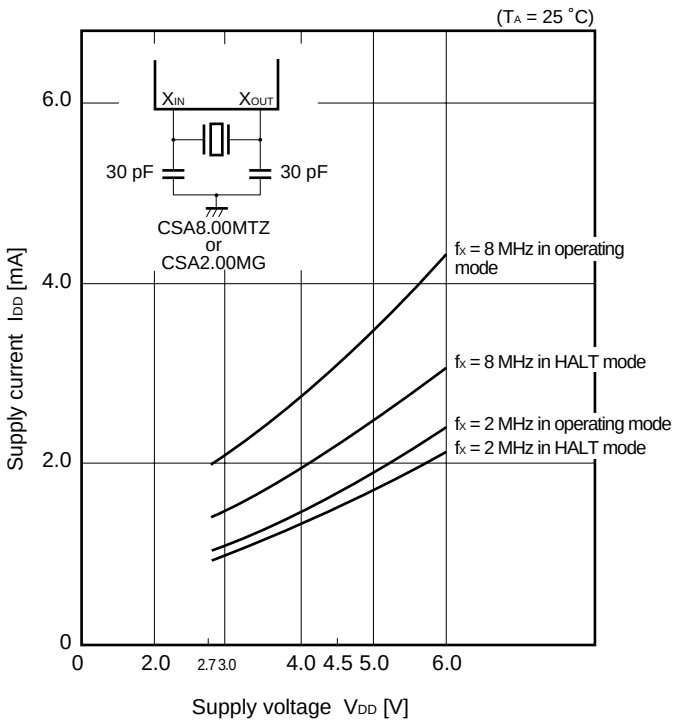


Read program memory timing

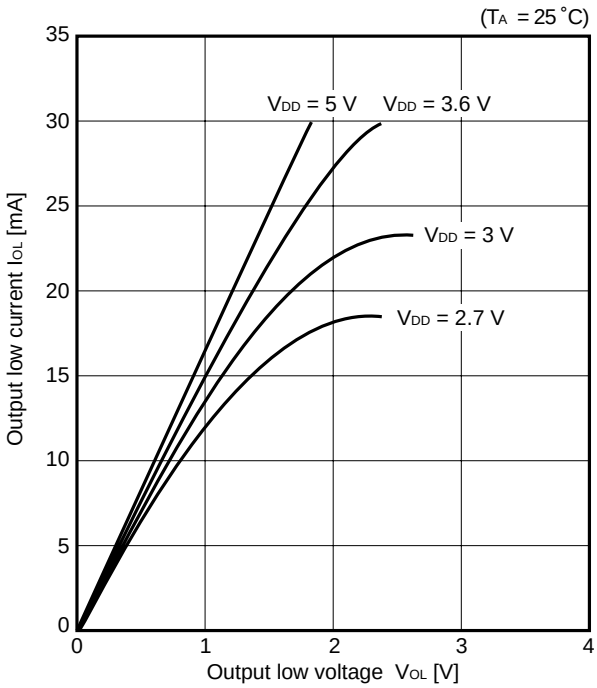


★ 5. CHARACTERISTIC CURVES (FOR REFERENCE)

I_{DD} vs V_{DD}

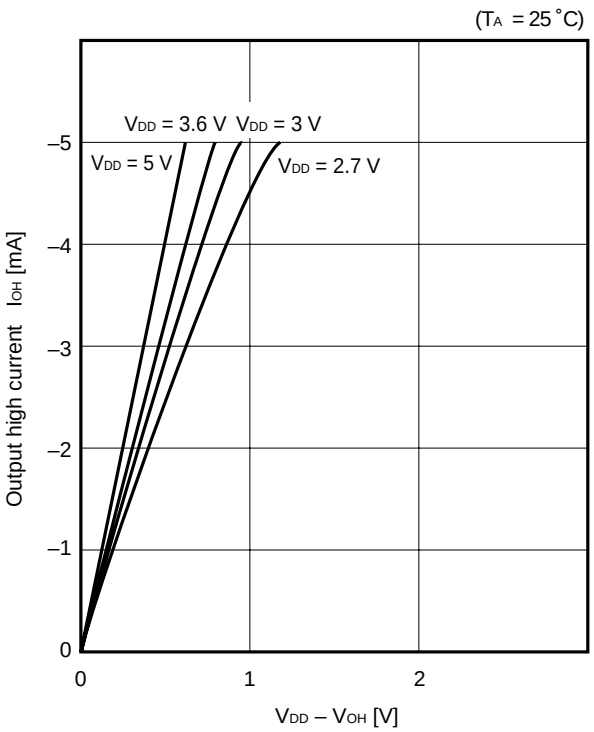


I_{OL} vs. V_{OL}



Caution The absolute maximum rating of the current is 30 mA per pin.

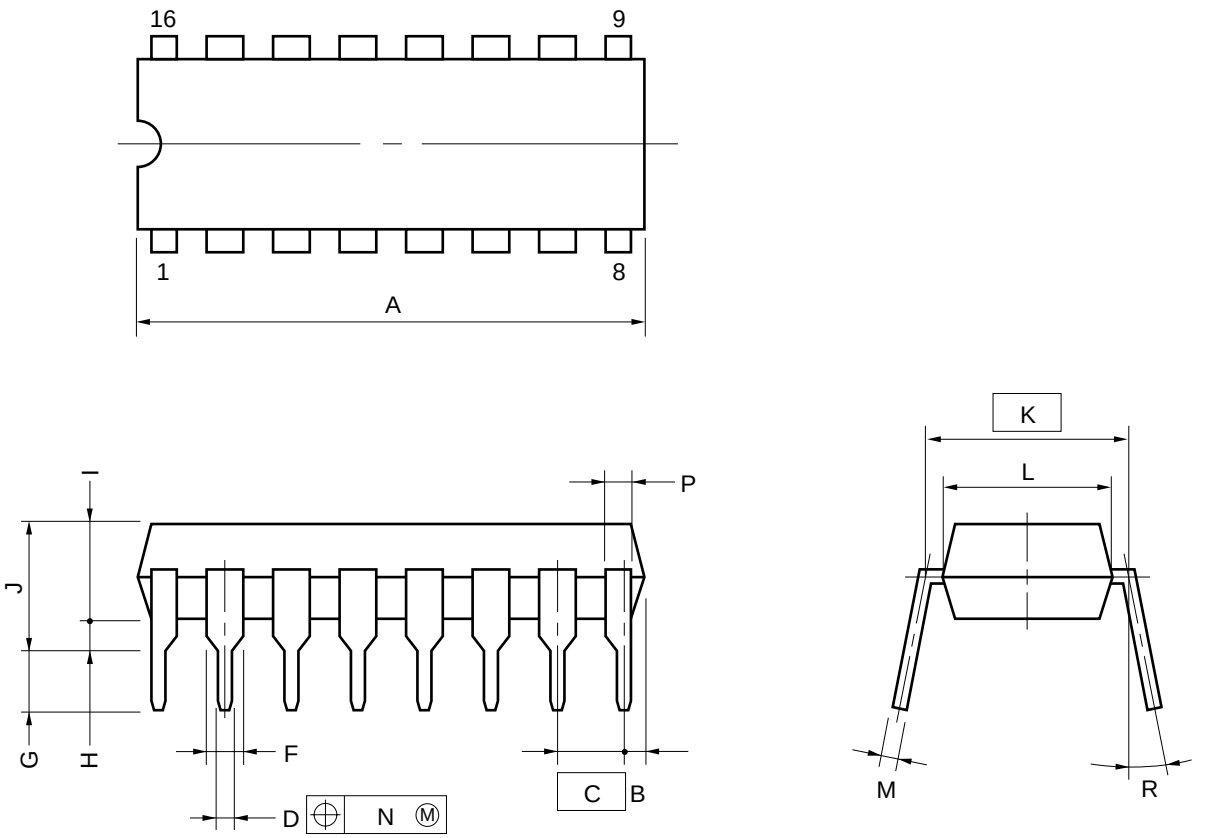
I_{OH} vs. (V_{DD} – V_{OH})



Caution The absolute maximum rating of the current is –5 mA per pin.

6. PACKAGE DRAWINGS

16 PIN PLASTIC DIP (300 mil)



NOTES

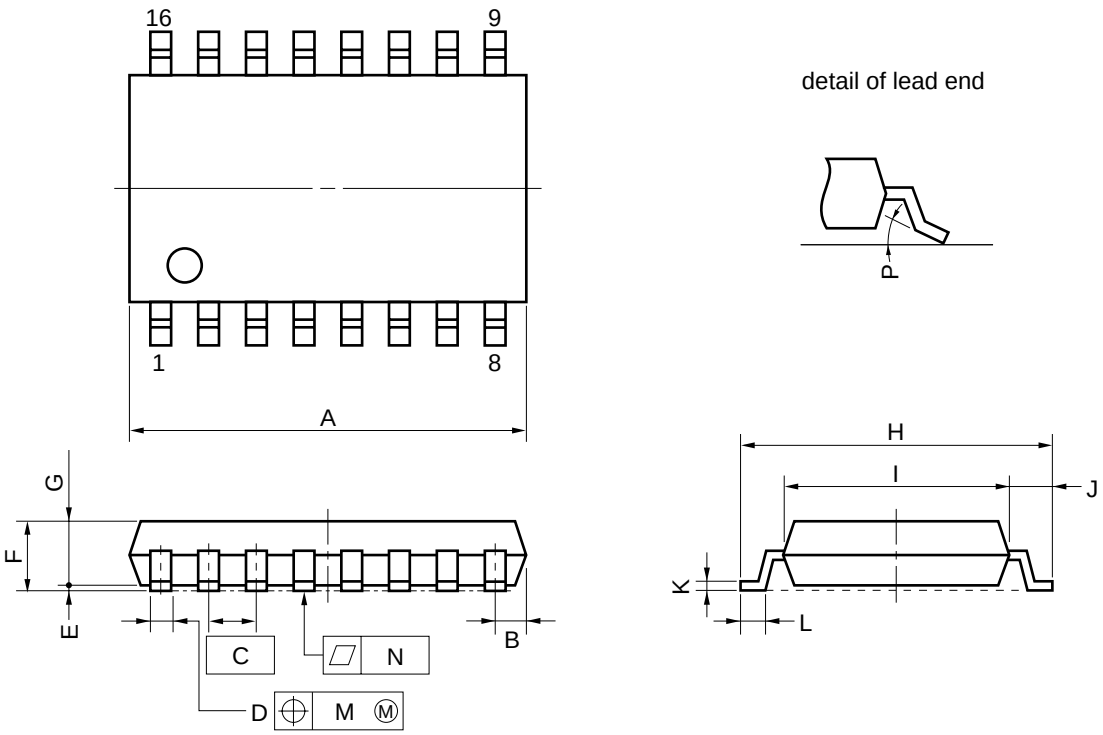
1) Each lead centerline is located within 0.25 mm (0.01 inch) of its true position (T.P.) at maximum material condition.

2) Item "K" to center of leads when formed parallel.

ITEM	MILLIMETERS	INCHES
A	20.32 MAX.	0.800 MAX.
B	1.27 MAX.	0.050 MAX.
C	2.54 (T.P.)	0.100 (T.P.)
D	0.50 ± 0.10	$0.020^{+0.004}_{-0.005}$
F	1.1 MIN.	0.043 MIN.
G	3.5 ± 0.3	0.138 ± 0.012
H	0.51 MIN.	0.020 MIN.
I	4.31 MAX.	0.170 MAX.
J	5.08 MAX.	0.200 MAX.
K	7.62 (T.P.)	0.300 (T.P.)
L	6.5	0.256
M	$0.25^{+0.10}_{-0.05}$	$0.010^{+0.004}_{-0.003}$
N	0.25	0.01
P	1.1 MIN.	0.043 MIN.
R	0 ′15°	0 ′15°

P16C-100-300B-1

16 PIN PLASTIC SOP (300 mil)



NOTE

Each lead centerline is located within 0.12 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
A	10.46 MAX.	0.412 MAX.
B	0.78 MAX.	0.031 MAX.
C	1.27 (T.P.)	0.050 (T.P.)
D	$0.40^{+0.10}_{-0.05}$	$0.016^{+0.004}_{-0.003}$
E	0.1±0.1	0.004±0.004
F	1.8 MAX.	0.071 MAX.
G	1.55	0.061
H	7.7±0.3	0.303±0.012
I	5.6	0.220
J	1.1	0.043
K	$0.20^{+0.10}_{-0.05}$	$0.008^{+0.004}_{-0.002}$
L	0.6±0.2	$0.024^{+0.008}_{-0.009}$
M	0.12	0.005
N	0.10	0.004
P	$3^{\circ}{}^{+7^{\circ}}_{-3^{\circ}}$	$3^{\circ}{}^{+7^{\circ}}_{-3^{\circ}}$

P16GM-50-300B-4

7. RECOMMENDED SOLDERING CONDITIONS

The conditions listed below shall be met when soldering the μPD17P103.

For details of the recommended soldering conditions, refer to our document *SMD Surface Mount Technology Manual* (IEI-1207).

Please consult with our sales offices in case any other soldering process is used, or in case soldering is done under different conditions.

Table 7-1 Soldering Conditions for Surface-Mount Devices

μPD17P103GS: 16-pin plastic SOP (300 mil)

Soldering process	Soldering conditions
Partial heating method	Terminal temperature: 300 °C or less Flow time: 3 seconds or less (for each side of device)

Table 7-2 Soldering Conditions for Through Hole Mount Devices

μPD17P103CX: 16-pin plastic DIP (300 mil)

Soldering process	Soldering conditions
Wave soldering (only for terminals)	Solder temperature: 260 °C or less Flow time: 10 seconds or less
Partial heating method	Terminal temperature: 300 °C or less Flow time: 3 seconds or less (for each terminal)

Caution In wave soldering, apply solder only to the terminals. Care must be taken that jet solder does not come in contact with the main body of the package.

APPENDIX A TINY MICROCONTROLLER FAMILY

Item \ Product name	μPD17103	μPD17103L	μPD17P103	μPD17104	μPD17104L	μPD17P104
ROM capacity	Masked ROM		One-time PROM	Masked ROM		One-time PROM
	1K byte (512 × 16 bits)					
RAM capacity	16 × 4 bits					
Number of input/output port pins[Note]	11 (3)			16 (4)		
System clock	Ceramic oscillation					
Instruction execution time	2 μs (at f_X = 8 MHz)	8 μs (at f_X = 2 MHz)	2 μs (at f_X = 8 MHz)		8 μs (at f_X = 2 MHz)	2 μs (at f_X = 8 MHz)
Standby function	HALT, STOP					
Supply voltage	• 2.7 to 6.0 V (at f_X = 500 kHz to 2 MHz) • 4.5 to 6.0 V (at f_X = 500 kHz to 8 MHz)	• 1.8 to 3.6 V (at f_X = 500 kHz to 2 MHz)	• 2.7 to 6.0 V (at f_X = 500 kHz to 2 MHz) • 4.5 to 6.0 V (at f_X = 500 kHz to 8 MHz)		• 1.8 to 3.6 V (at f_X = 500 kHz to 2 MHz)	• 2.7 to 6.0 V (at f_X = 500 kHz to 2 MHz) • 4.5 to 6.0 V (at f_X = 500 kHz to 8 MHz)
Package	• 16-pin DIP • 16-pin SOP			• 22-pin shrink DIP		• 24-pin SOP
One-time PROM	μPD17P103		—	μPD17P104		—

Item \ Product name	μPD17107	μPD17107L	μPD17P107	μPD17108	μPD17108L	μPD17P108
ROM capacity	Masked ROM		One-time PROM	Masked ROM		One-time PROM
	1K byte (512 × 16 bits)					
RAM capacity	16 × 4 bits					
Number of input/output port pins[Note]	11 (3)			16 (4)		
System clock	RC oscillation					
Instruction execution time	8 μs (at f_{CC} = 1 MHz)	40 μs (at f_{CC} = 200 kHz)	8 μs (at f_{CC} = 1 MHz)		40 μs (at f_{CC} = 200 kHz)	8 μs (at f_{CC} = 1 MHz)
Standby function	HALT, STOP					
Supply voltage	• 2.5 to 6.0 V (at f_{CC} = 50 kHz to 250 kHz) • 4.5 to 6.0 V (at f_{CC} = 50 kHz to 1 MHz)	• 1.5 to 3.6 V (at f_{CC} = 50 kHz to 250 kHz)	• 2.5 to 6.0 V (at f_{CC} = 50 kHz to 250 kHz) • 4.5 to 6.0 V (at f_{CC} = 50 kHz to 1 MHz)		• 1.5 to 3.6 V (at f_{CC} = 50 kHz to 250 kHz)	• 2.5 to 6.0 V (at f_{CC} = 50 kHz to 250 kHz) • 4.5 to 6.0 V (at f_{CC} = 50 kHz to 1 MHz)
Package	• 16-pin DIP • 16-pin SOP			• 22-pin shrink DIP		• 24-pin SOP
One-time PROM	μPD17P107		—	μPD17P108		—

Note A number enclosed in parentheses indicates the number of the N-ch open-drain outputs. N-ch open-drain outputs can be connected to internal pull-up resistors by specifying the mask option.

Remark The μPD17P103 can be used to evaluate programs for the μPD17103L. Note, however, that the allowable supply voltages for the μPD17P103 and μPD17103L do not fall in the same range.

APPENDIX B DEVELOPMENT TOOLS

The following support tools are available for developing programs for the μPD17P103.

Hardware

Name	Description
In-circuit emulator [IE-17K IE-17K-ET**Note 1** EMU-17K**Note 2**]	The IE-17K, IE-17K-ET, and EMU-17K are in-circuit emulators applicable to the 17K series. The IE-17K and IE-17K-ET are connected to the PC-9800 series (host machine) or IBM PC/AT™ through the RS-232-C interface. The EMU-17K is inserted into the extension slot of the PC-9800 series (host machine). Use the system evaluation board (SE board) corresponding to each product together with one of these in-circuit emulators. *SIMPLEHOST*®, a man machine interface, implements an advanced debug environment. The EMU-17K also enables user to check the contents of the data memory in real time.
SE board (SE-17103L)	The SE-17103L is an SE board for the μPD17103, μPD17103L, or μPD17P103. It is used solely for evaluating the system. It is also used for debugging in combination with the in-circuit emulator.
Emulation probe (EP-17103CX)	The EP-17103CX is an emulation probe for the μPD17103, μPD17103L, μPD17P103, μPD17107, μPD17107L, or μPD17P107.
PROM programmer [AF-9703**Note 3** AF-9704**Note 3** AF-9705**Note 3** AF-9706**Note 3**]	The AF-9703, AF-9704, AF-9705, and AF-9706 are PROM programmers for the μPD17P103. Use one of these PROM programmers with the program adapter, AF-9799, to write a program into the μPD17P103.
Program adapter (AF-9799**Note 3**)	The AF-9799 is a socket unit for the μPD17P103, μPD17P104, μPD17P107 or μPD17P108. It is used with the AF-9703, AF-9704, AF-9705, or AF-9706.

Notes 1. Low-end model, operating on an external power supply

2. The EMU-17K is a product of I.C Corporation. Contact I.C Corporation. (Tokyo, 03-3447-3793) for details.

3. The AF-9703, AF-9704, AF-9705, AF-9706, and AF-9799 are products of Ando Electric Co., Ltd. Contact Ando Electric Co., Ltd. (Tokyo, 03-3733-1163) for details.

Software

Name	Description	Host machine	OS		Distribution media	Part number
17K series assembler (AS17K)	AS17K is an assembler applicable to the 17K series. In developing μPD17P103 programs, AS17K is used in combination with a device file (AS17103).	PC-9800 series	MS-DOS™		5.25-inch, 2HD	μS5A10AS17K
					3.5-inch, 2HD	μS5A13AS17K
		IBM PC/AT	PC DOS™		5.25-inch, 2HC	μS7B10AS17K
					3.5-inch, 2HC	μS7B13AS17K
Device file (AS17103)	AS17103 contains a device file for the μPD17103. It is used together with the assembler (AS17K), which is applicable to the 17K series.	PC-9800 series	MS-DOS		5.25-inch, 2HD	μS5A10AS17103 **Note**
					3.5-inch, 2HD	μS5A13AS17103 **Note**
		IBM PC/AT	PC DOS		5.25-inch, 2HC	μS7B10AS17103 **Note**
					3.5-inch, 2HC	μS7B13AS17103 **Note**
Support software (*SIMPLEHOST*)	*SIMPLEHOST*, running under Windows™, provides man-machine-interface in developing programs by using a personal computer and in-circuit emulator.	PC-9800 series	MS-DOS	Windows	5.25-inch, 2HD	μS5A10IE17K
					3.5-inch, 2HD	μS5A13IE17K
		IBM PC/AT	PC DOS		5.25-inch, 2HC	μS7B10IE17K
					3.5-inch, 2HC	μS7B13IE17K

Note The μS××××AS17103 contains μPD17103, μPD17104, μPD17107, μPD17108, μPD17103L, μPD17104L, μPD17107L, and μPD17108L.

Remark The following table lists the versions of the operating systems described in the above table.

OS	Versions
MS-DOS	Ver. 3.30 to Ver. 5.00A**Note**
PC DOS	Ver. 3.1 to Ver. 5.0**Note**
Windows	Ver. 3.0 to Ver. 3.1

Note MS-DOS versions 5.00 and 5.00A and PC DOS Ver. 5.0 are provided with a task swap function. This function, however, cannot be used in these software packages.

Cautions on CMOS Devices

① **Countermeasures against static electricity for all MOSs**

Caution When handling MOS devices, take care so that they are not electrostatically charged.

Strong static electricity may cause dielectric breakdown in gates. When transporting or storing MOS devices, use conductive trays, magazine cases, shock absorbers, or metal cases that NEC uses for packaging and shipping. Be sure to ground MOS devices during assembling. Do not allow MOS devices to stand on plastic plates or do not touch pins.

Also handle boards on which MOS devices are mounted in the same way.

② **CMOS-specific handling of unused input pins**

Caution Hold CMOS devices at a fixed input level.

Unlike bipolar or NMOS devices, if a CMOS device is operated with no input, an intermediate-level input may be caused by noise. This allows current to flow in the CMOS device, resulting in a malfunction. Use a pull-up or pull-down resistor to hold a fixed input level. Since unused pins may function as output pins at unexpected times, each unused pin should be separately connected to the V_{DD} or GND pin through a resistor.

If handling of unused pins is documented, follow the instructions in the document.

③ **Statuses of all MOS devices at initialization**

Caution The initial status of a MOS device is unpredictable when power is turned on.

Since characteristics of a MOS device are determined by the amount of ions implanted in molecules, the initial status cannot be determined in the manufacture process. NEC has no responsibility for the output statuses of pins, input and output settings, and the contents of registers at power on. However, NEC assures operation after reset and items for mode setting if they are defined.

When you turn on a device having a reset function, be sure to reset the device first.

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